NSN 5961-01-186-8316



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View Online at https://aerobasegroup.com/nsn/5961-01-186-8316

Inclosure Material:
Metal

Overall Length:
0.900 inches

Overall Height:
0.225 inches

Overall Width:
0.405 inches

End Application:
Radar system an/fps-117

Mounting Facility Quantity:
2
Internal Configuration:
Junction contact

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

65.0 collector to base voltage/static/emitter open and 65.0 collector to emitter voltage, dc with base short-circuited to emitter and 3.5 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

5.00 milliamperes zero-gate-voltage source current preset and 12.50 milliamperes zero-gate-voltage source current minor

Power Rating Per Characteristic:

750.0 watts small-signal input power, common-collector absolute

Transfer Ratio:

120.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

Flange, base and leads plated; cap plating option gold

Precious Material:

Gold

Terminal Type And Quantity:

1 case and 2 ribbon

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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